



### General Description

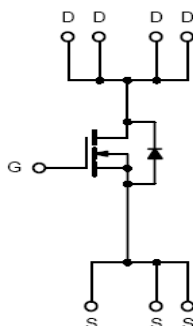
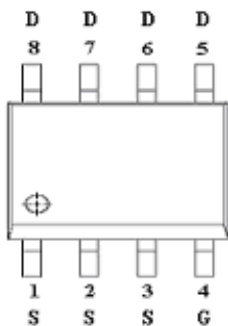
AFN4850WS, N-Channel enhancement mode MOSFET, uses Advanced Trench Technology to provide excellent  $R_{DS(ON)}$ , low gate charge.

These devices are particularly suited for low voltage power management, and low in-line power loss are needed in commercial industrial surface mount applications.

### Features

- 60V/8.5A,  $R_{DS(ON)}=20m\Omega@V_{GS}=10V$
- 60V/7.2A,  $R_{DS(ON)}=28m\Omega@V_{GS}=4.5V$
- Super high density cell design for extremely low  $R_{DS(ON)}$
- SOP-8P package design

### Pin Description ( SOP-8P )



### Application

- Motor and Load Control
- Power Management in White LED System
- Push Pull Converter
- LCD TV Inverter & AD/DC Inverter Systems.

### Pin Define

Pin	Symbol	Description
1	S	Source
2	S	Source
3	S	Source
4	G	Gate
5	D	Drain
6	D	Drain
7	D	Drain
8	D	Drain

### Ordering Information

Part Ordering No.	Part Marking	Package	Unit	Quantity
AFN4850WSS8RG	4850WS	SOP-8P	Tape & Reel	2500 EA

- ※ A Lot code
- ※ B Date code
- ※ AFN4850WSS8RG : 13" Tape & Reel ; Pb- Free ; Halogen- Free



### ※ Absolute Maximum Ratings

(T<sub>A</sub>=25°C Unless otherwise noted)

Parameter	Symbol	Typical	Unit
Drain-Source Voltage	V <sub>DSS</sub>	60	V
Gate –Source Voltage	V <sub>GSS</sub>	±20	V
Continuous Drain Current(T <sub>J</sub> =150°C)	I <sub>D</sub>	T <sub>A</sub> =25°C	8.5
		T <sub>A</sub> =70°C	7.2
Pulsed Drain Current	I <sub>DM</sub>	40	A
Continuous Source Current(Diode Conduction)	I <sub>S</sub>	1.5	A
Power Dissipation	P <sub>D</sub>	T <sub>A</sub> =25°C	2.8
		T <sub>A</sub> =70°C	1.8
Operating Junction Temperature	T <sub>J</sub>	150	°C
Storage Temperature Range	T <sub>STG</sub>	-55/150	°C
Thermal Resistance-Junction to Ambient	R <sub>θJA</sub>	62.5	°C/W

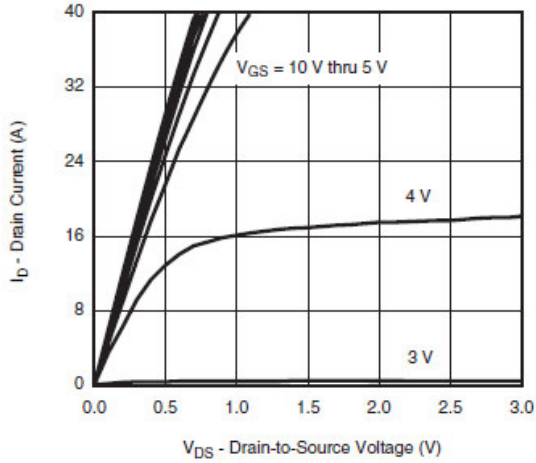
### Electrical Characteristics

(T<sub>A</sub>=25°C Unless otherwise noted)

Parameter	Symbol	Conditions	Min.	Typ	Max.	Unit
<b>Static</b>						
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	60			V
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250uA	1.0		2.0	
Gate Leakage Current	I <sub>GSS</sub>	V <sub>DS</sub> =0V, V <sub>GS</sub> =±20V			±100	nA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =48V, V <sub>GS</sub> =0V			1	uA
		V <sub>DS</sub> =48V, V <sub>GS</sub> =0V T <sub>J</sub> =85°C			5	
On-State Drain Current	I <sub>D(on)</sub>	V <sub>DS</sub> ≥ 5V, V <sub>GS</sub> =10V	40			A
Drain-Source On-Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =8.5A		13	20	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =7.2A		16	28	
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> =15V, I <sub>D</sub> =6.0A		25		S
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =1.7A, V <sub>GS</sub> =0V		0.8	1.2	V
<b>Dynamic</b>						
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =30V, V <sub>GS</sub> =10V I <sub>D</sub> ≅5.6A		20	30	nC
Gate-Source Charge	Q <sub>gs</sub>			4		
Gate-Drain Charge	Q <sub>gd</sub>			6		
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =30V, V <sub>GS</sub> =0V f=1MHz		3200		pF
Output Capacitance	C <sub>oss</sub>			300		
Reverse Transfer Capacitance	C <sub>rss</sub>			250		
Turn-On Time	t <sub>d(on)</sub>	V <sub>DD</sub> =30V, R <sub>L</sub> =30Ω I <sub>D</sub> ≅1A, V <sub>GEN</sub> =10V R <sub>G</sub> =6Ω		10	20	ns
	t <sub>r</sub>			10	20	
Turn-Off Time	t <sub>d(off)</sub>			25	50	
	t <sub>f</sub>			15	25	

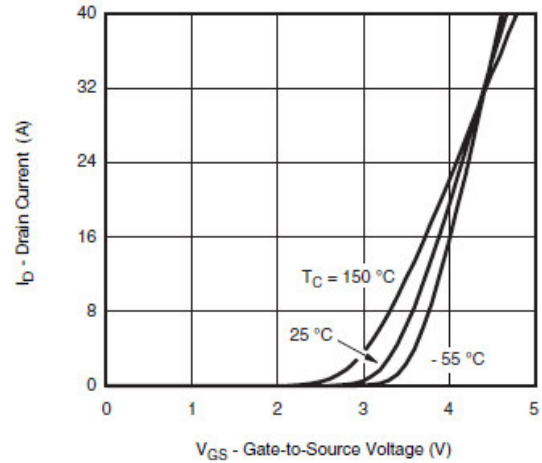


## Typical Characteristics



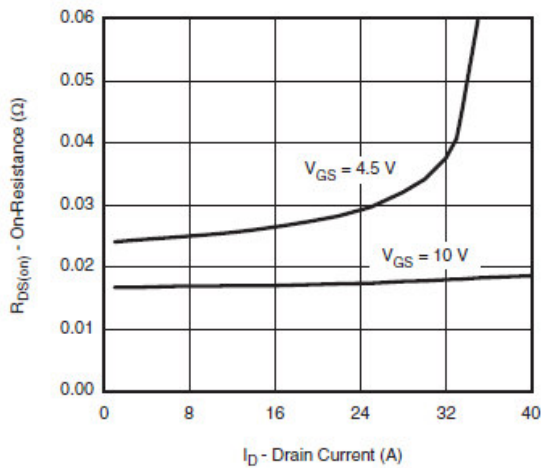
$V_{DS}$  - Drain-to-Source Voltage (V)

Output Characteristics



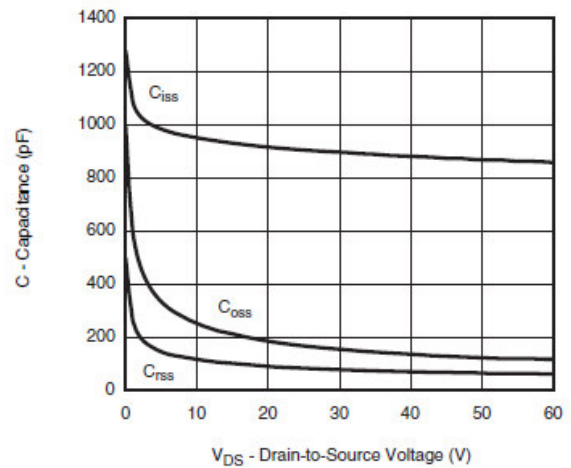
$V_{GS}$  - Gate-to-Source Voltage (V)

Transfer Characteristics



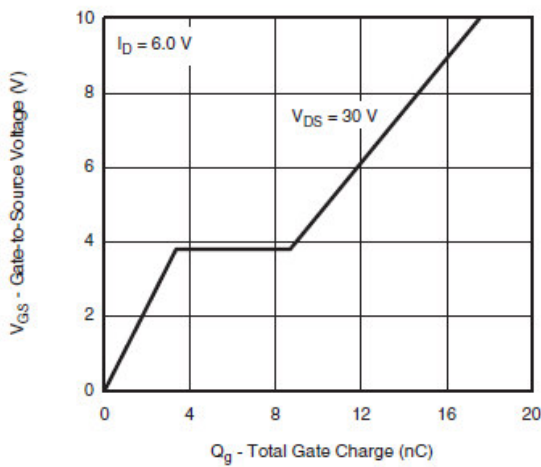
$I_D$  - Drain Current (A)

On-Resistance vs. Drain Current



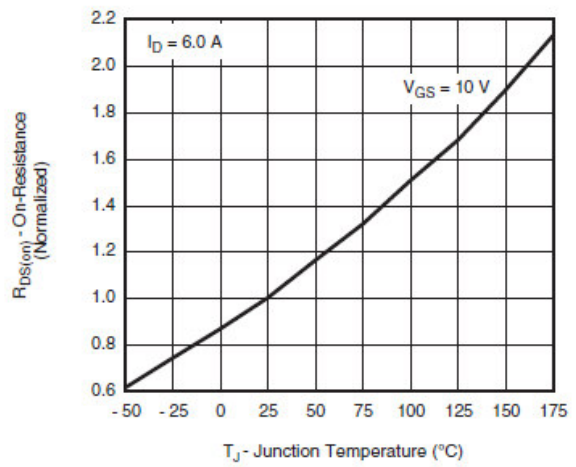
$V_{DS}$  - Drain-to-Source Voltage (V)

Capacitance



$Q_g$  - Total Gate Charge (nC)

Gate Charge

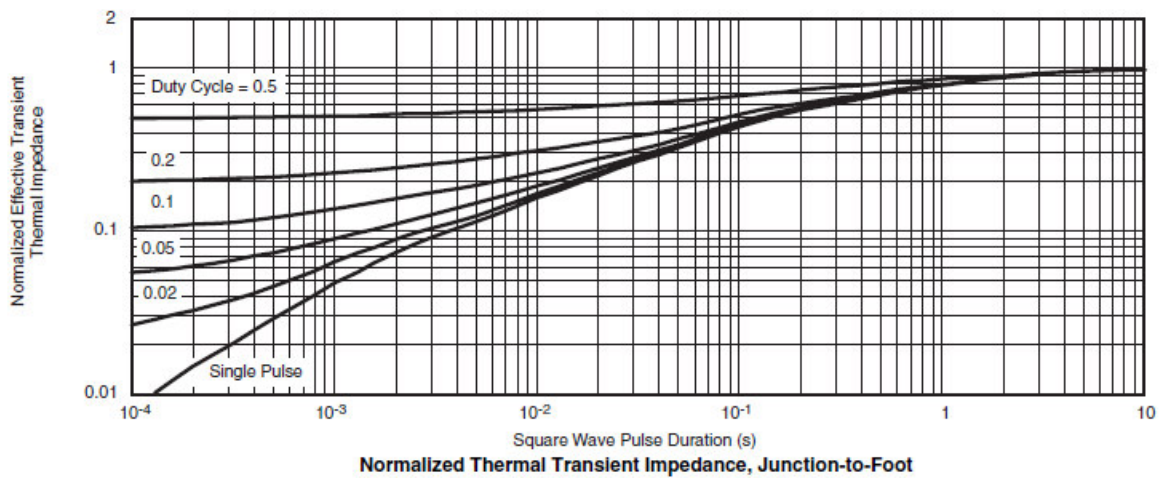
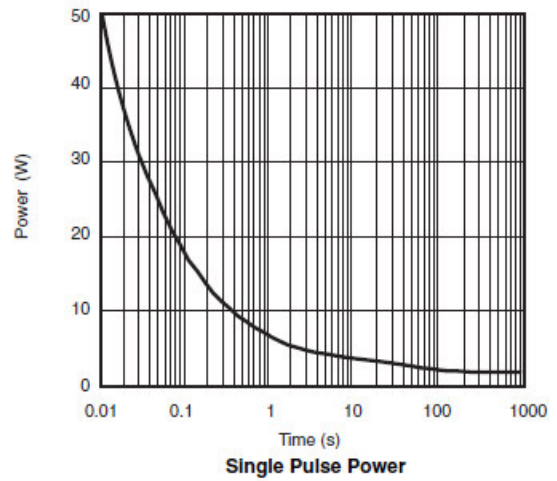
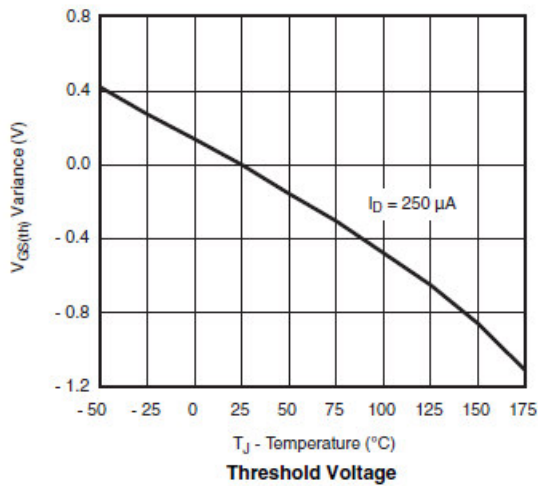
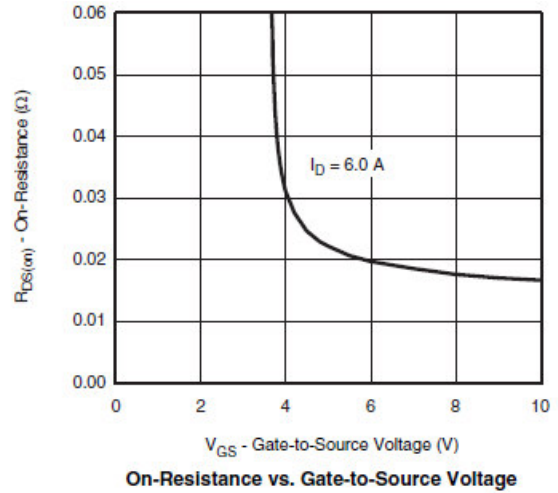
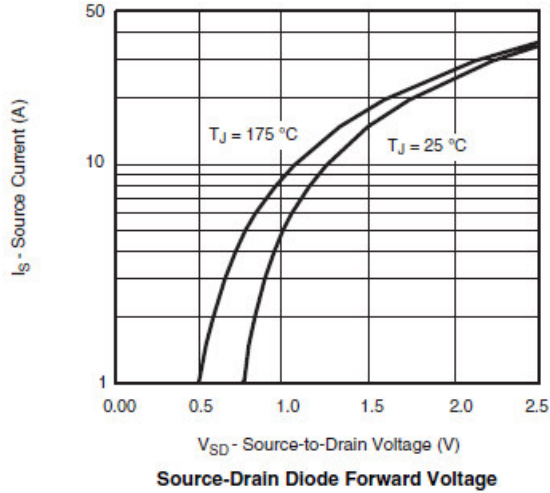


$T_J$  - Junction Temperature ( $^\circ\text{C}$ )

On-Resistance vs. Junction Temperature



## Typical Characteristics





**Typical Characteristics**

Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms

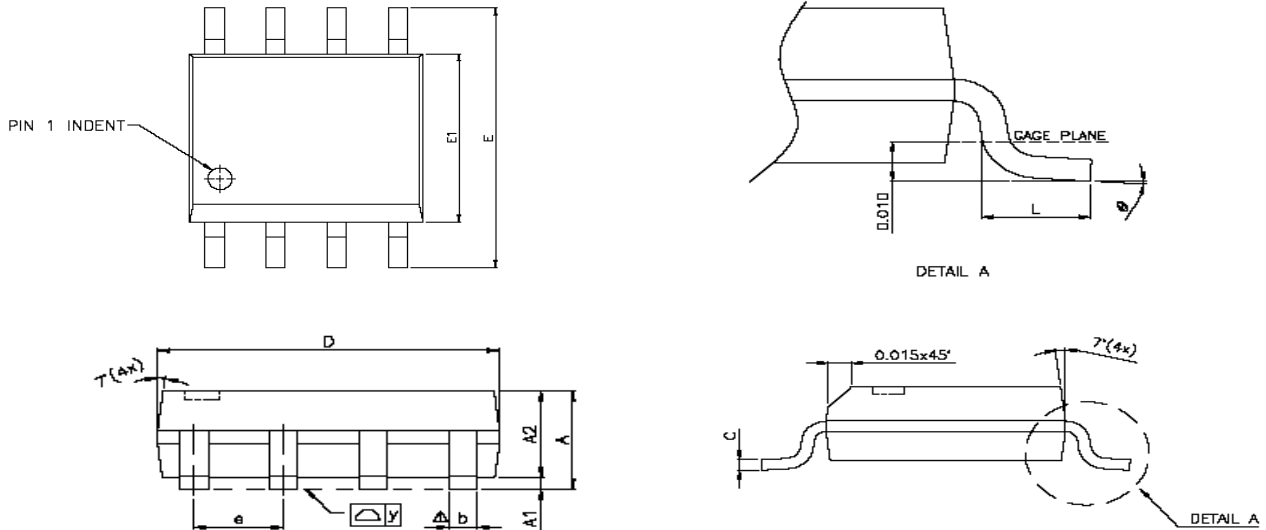


Unclamped Inductive Switching Test Circuit & Waveforms





**Package Information ( SOP-8P )**



SYMBOLS	DIMENSIONS IN MILLIMETERS			DIMENSIONS IN INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	1.47	1.60	1.73	0.058	0.063	0.068
A1	0.10	—	0.25	0.004	—	0.010
A2	—	1.45	—	—	0.057	—
b	0.33	0.41	0.51	0.013	0.016	0.020
C	0.19	0.20	0.25	0.0075	0.008	0.0098
D	4.80	4.85	4.95	0.189	0.191	0.195
E	5.80	6.00	6.20	0.228	0.236	0.244
E1	3.80	3.90	4.00	0.150	0.154	0.157
e	—	1.27	—	—	0.050	—
L	0.38	0.71	1.27	0.015	0.028	0.050
$\Delta y$	—	—	0.076	—	—	0.003
$\theta$	0°	—	8°	0°	—	8°

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